

Notice of References Cited	Application/Control No. 10/620,430	Applicant(s)/Patent Under Reexamination INOUE ET AL.	
	Examiner Belur V Keshavan	Art Unit 2825	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-5,192,987	03-1993	Khan et al.	257/183.1
	B	US-5,296,395	03-1994	Khan et al.	438/149
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Masato et al., Novel High Drain Breakdown Voltage AlGaIn/GaN HFETs using Selective Thermal Oxidation Process., IEEE IEDM 00-377
	V	Sullivan et al., High-Power 10 GHz Operation of AlGaIn HFET's on Insulating SiC., IEEE Elect.Device Letters., Vol. 19, No 6, June 1998
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.